

Field Effect Transistor

Silicon N Channel MOS Type (L^2 - π -MOS IV)

High Speed, High Current DC-DC Converter,
Relay Drive and Motor Drive Applications

Features

- 4-Volt Gate Drive
- Low Drain-Source ON Resistance
 - $R_{DS(ON)} = 0.28\Omega$ (Typ.)
- High Forward Transfer Admittance
 - $|Y_{fs}| = 1.6S$ (Typ.)
- Low Leakage Current
 - $I_{DSS} = 100\mu A$ (Max.) @ $V_{DS} = 60V$
- Enhancement-Mode
 - $V_{th} = 0.8 \sim 2.0V$ @ $V_{DS} = 10V$, $I_D = 1mA$

Absolute Maximum Ratings ($T_a = 25^\circ C$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		V_{DSS}	60	V
Drain-Gate Voltage ($R_{GS} = 20k\Omega$)		V_{DGR}	60	V
Gate-Source Voltage		V_{GSS}	± 20	V
Drain Current	DC	I_D	2	A
	Pulse	I_{DP}	6	
Drain Power Dissipation ($T_a = 25^\circ C$)		P_D	0.5	W
Drain Power Dissipation		P_{D^*}	1.5	W
Channel Temperature		T_{ch}	150	$^\circ C$
Storage Temperature Range		T_{stg}	$-55 \sim 150$	$^\circ C$

P_{D^*} : Mounted on ceramic substrate (600 mm² x 0.8t)

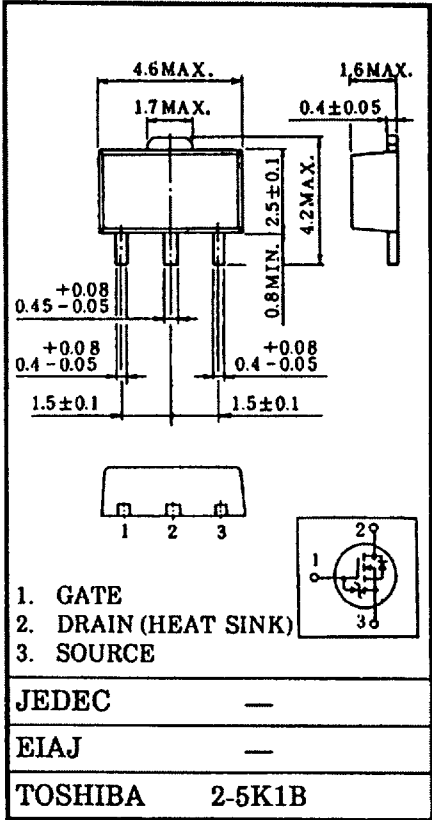
Thermal Characteristics

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	250	$^\circ C/W$

This transistor is an electrostatic sensitive device. Please handle with care.

Industrial Applications

Unit in mm

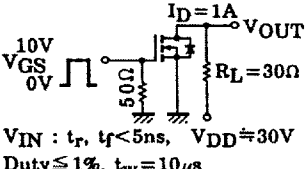


Weight : 0.05g

Marking



Electrical Characteristics (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GSS}	$V_{GS} = \pm 16V, V_{DS} = 0V$	—	—	± 10	μA
Drain Cut-off Current		I_{DSS}	$V_{DS} = 60V, V_{GS} = 0V$	—	—	100	μA
Drain-Source Breakdown Voltage		$V_{(BR) DSS}$	$I_D = 10mA, V_{GS} = 0V$	60	—	—	V
Gate Threshold Voltage		V_{th}	$V_{DS} = 10V, I_D = 1mA$	0.8	—	2.0	V
Drain-Source ON Resistance		$R_{DS(ON)}$	$V_{GS} = 4V, I_D = 1A$	—	0.39	0.53	Ω
			$V_{GS} = 10V, I_D = 1A$	—	0.28	0.37	
Forward Transfer Admittance		$ Y_{fs} $	$V_{DS} = 10V, I_D = 1A$	1.0	1.6	—	S
Input Capacitance		C_{iss}	$V_{DS} = 10V, V_{GS} = 0V,$ $f = 1MHz$	—	125	180	pF
Reverse Transfer Capacitance		C_{rss}		—	30	60	
Output Capacitance		C_{oss}		—	85	130	
Switching Time	Rise Time	t_r	 $I_D = 1A$ $V_{GS} = 10V$ $V_{DS} = 10V$ $R_L = 30\Omega$ $V_{IN} : t_r, t_f < 5ns, V_{DD} \approx 30V$ Duty $\leq 1\%, t_w = 10\mu s$	—	30	60	ns
	Turn-on Time	t_{on}		—	60	120	
	Fall Time	t_f		—	40	80	
	Turn-off Time	t_{off}		—	135	270	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Q_g	$V_{DD} = 48V, V_{GS} = 10V,$ $I_D = 2A$	—	6.5	13	nC
Gate-Source Charge		Q_{gs}		—	4.5	—	
Gate-Drain ("Miller") Charge		Q_{gd}		—	2.0	—	

Source-Drain Diode Ratings and Characteristics (Ta = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I_{DR}	—	—	—	2	A
Pulse Drain Reverse Current	I_{DRP}	—	—	—	6	A
Diode Forward Voltage	V_{DSF}	$I_{DR} = 2A, V_{GS} = 0V$	—	—	-1.5	V
Reverse Recovery Time	t_{rr}	$I_{DR} = 2A, V_{GS} = 0V$	—	75	—	ns
Reverse Recovered Charge	Q_{rr}	$dI_{DR}/dt = 50A/\mu s$	—	75	—	μC

